RT1N44BX SERIES

(Transistor)

Transistor With Resistor For Switching Application

Silicon NPN Epitaxial Type

OUTLINE DRAWING DESCRIPTION UNIT:mm RT1N44BX is one chip transistor RT1N44BC with built-in bias resistor, PNP type is RT1P44BX. 2.8 0.65 1.5 0.65 FEATURE 0.95 0.4 ſ •Built-in bias resistor (R2=47k Ω). 1.90 2.8 0.95 (2)3 **APPLICATION** Inverted circuit, switching circuit, interface circuit, driver circuit. 0. 0 Equivalent circuit $0 \sim 0.1$ С (OUT) JEITA: SC-59 JEDEC: Similar to TO-236 В (IN) **Terminal Connector** R2 1):Base (2): Emitter Е 3: Collector (GND) RT1N44BU RT1N44BM RT1N44BS 2.1 4.0 1.5 0.425 1.25 0.425 0.35 0.8 0.35 7.5MAX 3.0 0.3 0.65 1 0.5 01 2.0 1.7 1.0 13.0MIN 0.65 3 14.0 0.45 0.9 0.7 0.55 0.15 0.7 2.5 2 1 0~0.1 0~0.1 JEITA: SC-75A JEITA: SC-70 JEITA: -JEDEC: -JEDEC : -JEDEC : -Terminal Connector **Terminal Connector Terminal Connector** 1):Base 1: Emitter 1):Base (2): Emitter 2: Emitter 2: Collector 3: Collector 3: Collector 3:Base

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〈Transistor〉 Transistor With Resistor For Switching Application

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MARKING

RT1N44BC RT1N44BM RT1N44BU	RT1N44BS
N W type name	type name Lot No.

MAXIMUM RATING (Ta=25°C)

SYMBOL	PARAMETER	RATING				
		RT1N44BU	RT1N44BM	RT1N44BC	RT1N44BS	UNIT
V _{CBO}	Collector to Base voltage	50				V
V _{EBO}	Emitter to Base voltage	6				V
V _{CEO}	Collector to Emitter voltage	50				V
Ι _c	Collector current	100				mA
I _{CM}	Peak Collector current	200				mA
Pc	Collector dissipation(Ta=25°C)	150	20	00	450	mW
Tj	Junction temperature	+150				°C
Tstg	Storage temperature	-55~+150				٦°

ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL PARAMETER	TEST CONDITION	LIMIT			UNIT	
	TEST CONDITION	MIN	TYP	MAX	UNIT	
$V_{(BR)CEO}$	C to E break down voltage	$I_{c}=100 \mu$ A, $R_{BE}=\infty$	50	—	—	V
I _{CBO}	Collector cut off current	V _{CB} =50V, I _E =0	-	—	0.1	μA
I _{EBO}	Emitter cut off current	V_{EB} =5V, I _c =0	80	106	154	μA
h _{FE}	DC forward current gain	V_{ce} =5V, I _c =5mA	68	—	—	—
V _{CE(sat)}	C to E saturation voltage	I _c =10mA, I _B =0.5mA	-	—	0.3	V
R ₂	Emitter-base resistor	—	33	47	61	kΩ
f⊤	Gain band width product	V _{CE} =6V, I _E =-10mA	-	200	—	MHz

RT1N44BX SERIES

Transistor With Resistor For Switching Application Silicon NPN Epitaxial Type



10

COLLECTOR CURRENT IC(mA)

0.01 1



COLLECTOR CURRENT VS INPUT OFF VOLTAGE



100

(Transistor)

ISAHAYA ELECTRONICS CORPORATION

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